

Correction to High-Efficiency Colloidal Quantum Dot Photovoltaics via Robust Self-Assembled Monolayers

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In the original published paper, the Experimental Section of the paper described an incorrect protocol for the fabrication of the ZnO electrode. While this does not impact the conclusions of the work, the section of text is corrected here, and the author list is revised to include three authors who contributed to the development of the correct protocol.

Authors Lethy Krishnan Jagadamma from the King Abdullah University of Science and Technology (KAUST), Abdullah Saud Abbas from the University of Toronto, and Aram Amassian from KAUST have been added. A new affiliation for King Abdullah University of Science and Technology (KAUST) is also added. The complete author list with affiliations is shown correctly above in this Addition/Correction.

Additionally, on page 7695, in the ZnO Film Deposition section, the text should be corrected as follows:

ZnO Film Deposition. ZnO synthesis was based on a modification of a previously reported method.²¹ Briefly, 0.1 M of zinc acetate dehydrate and monoethanol amine in 2-methoxyethanol solution were mixed in a nitrogen-filled glove box. The resulting solution was gently shaken until fully dissolved and then kept at 30 °C during 24 h under vigorous stirring. ZnO films were fabricated in a two-step process: first, the ZnO solution was spin-cast on ITO substrates at 3000 rpm for 30 s and then was annealed at 200 °C for 10 min. A second layer of ZnO was then spin-cast and annealed at 250 °C for 20 min.

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